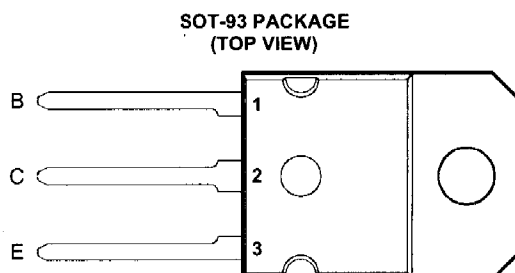


TIP36, TIP36A, TIP36B, TIP36C
PNP SILICON POWER TRANSISTORS

- Designed for Complementary Use with the TIP35 Series
- 125 W at 25°C Case Temperature
- 25 A Continuous Collector Current
- 40 A Peak Collector Current
- Customer-Specified Selections Available



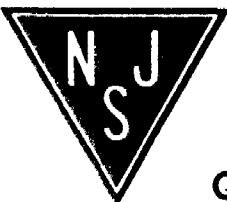
Pin 2 is in electrical contact with the mounting base.

MDTRAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIP36	V_{CBO}	-80	V
	TIP36A		-100	
	TIP36B		-120	
	TIP36C		-140	
Collector-emitter voltage ($I_B = 0$)	TIP36	V_{CEO}	-40	V
	TIP36A		-60	
	TIP36B		-80	
	TIP36C		-100	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-25	A
Peak collector current (see Note 1)		I_{CM}	-40	A
Continuous base current		I_B	-5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	125	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	90	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

- NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.
3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = -0.4$ A, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = -20$ V.



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

TIP36, TIP36A, TIP36B, TIP36C

PNP SILICON POWER TRANSISTORS

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -30 \text{ mA}$ (see Note 5) $I_B = 0$	TIP36 TIP36A TIP36B TIP36C		-40 -60 -80 -100	V
I_{CES} Collector-emitter cut-off current	$V_{CE} = -80 \text{ V}$ $V_{BE} = 0$ $V_{CE} = -100 \text{ V}$ $V_{BE} = 0$ $V_{CE} = -120 \text{ V}$ $V_{BE} = 0$ $V_{CE} = -140 \text{ V}$ $V_{BE} = 0$	TIP36 TIP36A TIP36B TIP36C		-0.7 -0.7 -0.7 -0.7	mA
I_{CEO} Collector cut-off current	$V_{CE} = -30 \text{ V}$ $I_B = 0$ $V_{CE} = -60 \text{ V}$ $I_B = 0$	TIP36/36A TIP36B/36C		-1 -1	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$ $I_C = 0$			-1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -4 \text{ V}$ $I_C = -1.5 \text{ A}$ $V_{CE} = -4 \text{ V}$ $I_C = -15 \text{ A}$	(see Notes 5 and 6)	25 10	50	
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -1.5 \text{ A}$ $I_C = -15 \text{ A}$ $I_B = -5 \text{ A}$ $I_C = -25 \text{ A}$	(see Notes 5 and 6)		-1.8 -4	V
V_{BE} Base-emitter voltage	$V_{CE} = -4 \text{ V}$ $I_C = -15 \text{ A}$ $V_{CE} = -4 \text{ V}$ $I_C = -25 \text{ A}$	(see Notes 5 and 6)		-2 -4	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$ $I_C = -1 \text{ A}$ $f = 1 \text{ kHz}$		25		
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$ $I_C = -1 \text{ A}$ $f = 1 \text{ MHz}$		3		

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †	MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -15 \text{ A}$ $I_{B(on)} = -1.5 \text{ A}$ $I_{B(off)} = 1.5 \text{ A}$		1.1		μs
t_{off} Turn-off time	$V_{BE(off)} = 4.15 \text{ V}$ $R_L = 2 \Omega$ $t_p = 20 \mu\text{s}$, $dc \leq 2\%$		0.8		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.